

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: To Be Assigned
Examiner: To Be Assigned

In re PATENT APPLICATION of:

Applicant(s) : Toshio NAGATA)	INFORMATION DISCLOSURE STATEMENT
Appln. No. : To Be Assigned)	
Filed : June 27, 2003)	
For : METHOD OF FABRICATING A SEMICONDUCTOR DEVICE INCLUDING A TUNNEL OXIDE FILM)	
Atty. Dkt. : MAE 286)	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

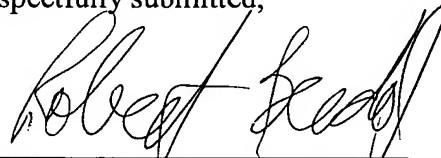
Sir:

This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(1).

Attached is a copy of a Japanese publication. Any relevance of the Japanese publication can be gleaned from the attached English-language Abstract. The document is listed on the attached Form PTO-1449.

Since this Information Disclosure Statement is being filed with the application, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to the document submitted. Consideration of the submitted document is respectfully requested.

Respectfully submitted,



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June 27, 2003
Date

RHB:tz

FEE ENCLOSED:\$ 790
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f t ur Deposit Account
N .18-0002

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT			Atty Docket	Application No.			
			MAE 286	To Be Assigned			
			Applicant				
			Toshio NAGATA				
			Filing Date	Group Unit			
			June 27, 2003	To Be Assigned			
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Trans-lation
	AH	08-255905	10/01/96				Abstract
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AO	James C.M. Hwang, "Relationship between gate lag, power drift, and power slump of pseudomorphic high electron-mobility transistors", Solid-State Electronics 43 (1999), pp. 1325-1331					
	AP						
	AQ						
	AR						
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							